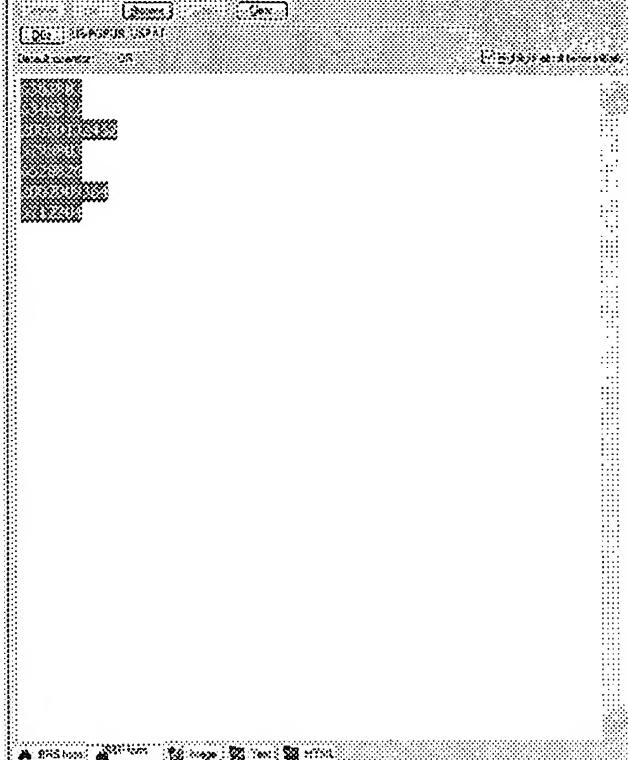


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 - L1: (13849) LDD or "lightly doped drain" or "lightly-doped-drain" or "lightly-doped-drain" or "a...
 - L2: (113707) <parent>
 - L3: (231) L1 with L2
 - L4: (4222592; @adv="20040121")
 - L5: (215) L3 and L4
 - L6: (61383883) or 634837 or 20030 (33432) or 1653887 or 2002039
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C	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval Cls	Inventor	S	C	P
1	<input checked="" type="checkbox"/> US 20030132432 A1 US 61383883 B2	20030717	21	Semiconductor device and method of producing the same	257/192			Enomoto, Masataka	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
2	<input checked="" type="checkbox"/> US 61383883 B2	20030904	32	Depletion type MOS semiconductor device and MOS power IC	257/147	257/133;		Yoshida, Kazuhiko et al	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>
3	<input checked="" type="checkbox"/> US 61383883 B1	20030507	6	Method of reducing junction capacitance of source/drain region	433/303	257/201-235;		Cheng, Yao-Chun et al	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input type="checkbox"/>

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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	13848	LD or "lightly doped drain" or "lightly-doped-drain" or "lightly-doped drain" or "lightly doped-drain"	US-PGPUB; USPAT	OR	ON	2005/03/11 09:40
L2	113707	deplet\$	US-PGPUB; USPAT	OR	ON	2005/03/11 09:40
L3	231	L1 with L2	US-PGPUB; USPAT	OR	ON	2005/03/11 09:40
L4	4222592	@ad<"20040121"	US-PGPUB; USPAT	OR	ON	2005/03/11 09:40
L5	215	L3 and L4	US-PGPUB; USPAT	OR	ON	2005/03/11 10:03
L6	6	(("6383883") or ("6348372") or ("20030132452") or ("5795803") or ("6528826") or ("2002009364") or ("5712204")).PN.	US-PGPUB; USPAT	OR	OFF	2005/03/11 10:08